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				U.S. PATENT DOCU	MENTS						
		DOCUMEN T NUMBER	DATE	NAME	CLASS	SUBCLASS		G DATE PROPRIATE			
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			FO	REIGN PATENT DO	CUMENTS						
DOCUMENT NUMBER		DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO					
	\Box										
		ОТ	HER (Inclu	ding Author, Title, Dat	e, Pertinent	Pages, Etc.)					
2M		Matthews, J. W. and Blakeslee, A. E., "Defects in Epitaxial Multilayers," Journal of Crystal Growth 27, (1974), pp. 118-125.									
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.



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	149 of Commerce ademark Office	Docket No). T004		SHEET 2. Serial No. Unassigned			8/01	
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الأذ	Qian et al., "1	.3µm Vertic	al-Cavity Surface-Emi Technology Letters, V	tting Lasers	with Double-Be	onded G	GaAs-AlAs Bragg		
		Uchiyam et al., "Continuous-Wave Operation up to 36°C of 1.3µm GaInAsP-InP Vertical-Cavity Surface-Emitting Lasers," <i>IEEE Photonics Technology Letters</i> , Vol. 9, No. 2, February 1997,							
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		Salet et al., "Undercut Ridge Structures: A Novel Approach to 1.3/1.55µm Vertical-Cavity Lasers Designed for Continuous-Wave Operation," <i>IEEE ProcOptoelectron.</i> , Vol. 145, No. 2, April 1998, pp. 125-131.							
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Form PTO-144 Department of Patent and Trace	Commerce	Docket No. PAT004			Serial No. Unassigned			
INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION (Use several sheets if necessary)		Applicants We	n-Yen Hwang		PT S S S S S S S S S S S S S S S S S S S			
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ŢV	Salet et al., "Gas-Source Molecular-Beam Epitaxy and Optical Characterisation of Highly-Reflective InGaAsP/InP Multilayer Bragg Mirrors for 1.3µm Vertical-Cavity Lasers," Electronics Letters., Vol. 33, No. 13, June 1997, pp. 1145-1147.							
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